

50 AMP SILICON BRIDGE RECTIFIERS

FEATURES

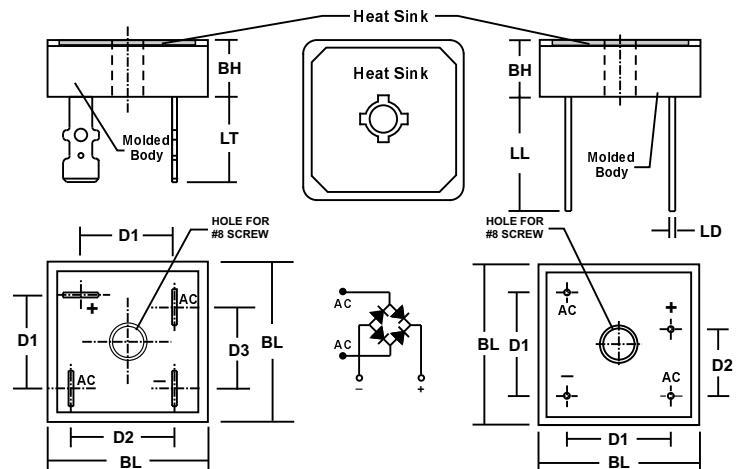
- **VOID FREE VACUUM DIE SOLDERING FOR MAXIMUM MECHANICAL STRENGTH AND HEAT DISSIPATION (Solder Voids: Typical < 2%, Max. < 10% of Die Area)**
- **BUILT-IN STRESS RELIEF MECHANISM FOR SUPERIOR RELIABILITY AND PERFORMANCE**
- **INTEGRALLY MOLDED HEAT SINK PROVIDES VERY LOW THERMAL RESISTANCE FOR MAXIMUM HEAT DISSIPATION**
- **UL RECOGNIZED - FILE #E124962**
- **RoHS COMPLIANT**

MECHANICAL DATA

- **Case:** Case: Molded epoxy with integral heat sink
Epoxy carries a U/L Flammability rating of 94V-0
- **Terminals:** Round silver plated copper pins or fast-on terminals
- **Soldering:** Per MIL-STD 202 Method 208 guaranteed
- **Polarity:** Marked on side of case
- **Mounting Position:** Any. Through hole for #8 screw.
Max. mounting torque = 20 in-lb.
- **Weight:** Fast-on Terminals - 0.7 Ounces (20.0 Grams)
Wire Leads - 0.55 Ounces (16.0 Grams)

MECHANICAL SPECIFICATION

SERIES: DB5000P - DB5010P and ADB5004P - ADB5008P



| SYM | MILLIMETERS | | INCHES | |
|-----|-------------|------|--------|------|
| | MIN | MAX | MIN | MAX |
| BL | 28.4 | 28.7 | 1.12 | 1.13 |
| BH | 9.6 | 10.2 | 0.38 | 0.40 |
| D1 | 15.7 | 16.7 | 0.62 | 0.66 |
| D2 | 17.5 | 18.5 | 0.69 | 0.73 |
| D3 | 13.5 | 14.5 | 0.53 | 0.57 |
| LT | n/a | 15.2 | n/a | 0.6 |

| SYM | MILLIMETERS | | INCHES | |
|-----|-------------|------|--------|-------|
| | MIN | MAX | MIN | MAX |
| BL | 28.4 | 28.7 | 1.12 | 1.13 |
| BH | 9.6 | 10.2 | 0.38 | 0.40 |
| D1 | 17.5 | 18.5 | 0.69 | 0.73 |
| D2 | 10.9 | 11.9 | 0.43 | 0.47 |
| LL | 20.6 | n/a | 0.81 | n/a |
| LD | 1.0 | 1.1 | 0.039 | 0.042 |

Suffix "T" indicates FAST-ON TERMINALS

Suffix "W" indicates WIRE LEADS

MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive loads, derate current by 20%.

| PARAMETER (TEST CONDITIONS) | SYMBOL | RATINGS | | | | | | | | | | UNITS |
|--|-----------------------|----------------------|-----------|-----------|--------------------------|--------------|----------|----------|----------|----------|----------|-------|
| | | CONTROLLED AVALANCHE | | | NON-CONTROLLED AVALANCHE | | | | | | | |
| | | ADB 5004P | ADB 5006P | ADB 5008P | DB 5000P | DB 5001P | DB 5002P | DB 5004P | DB 5006P | DB 5008P | DB 5010P | |
| Series Number | | | | | | | | | | | | |
| Maximum DC Blocking Voltage | V _{RM} | | | | | | | | | | | VOLTS |
| Working Peak Reverse Voltage | V _{RWM} | 400 | 600 | 800 | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | |
| Maximum Peak Recurrent Reverse Voltage | V _{RRM} | | | | | | | | | | | |
| RMS Reverse Voltage | V _R (RMS) | 280 | 420 | 560 | 35 | 70 | 140 | 280 | 420 | 560 | 700 | |
| Minimum Avalanche Voltage | V _(BR) Min | See Note 1 | | | n/a | | | | | | | VOLTS |
| Maximum Avalanche Voltage | V _(BR) Max | See Note 1 | | | n/a | | | | | | | |
| Forward Voltage Drop (Per Diode) at 25 Amps DC Max. Typ. | V _{FM} | | | | | 1.10 1.02 | | | | | | AMPS |
| Peak Forward Surge Current. Single 60Hz Half-Sine Wave Superimposed on Rated Load (JEDEC Method). T _J = 125° C | I _{FSM} | | | | | 600 | | | | | | |
| Average Forward Rectified Current @ T _c = 75° C | I _O | | | | | 50 | | | | | | |
| Junction Temperature Range | T _J | | | | | -55 to +135 | | | | | | °C |
| Storage Temperature Range | T _{STG} | | | | | -55 to +135 | | | | | | |
| Maximum Reverse Current at Rated V _{RM} @ T _A = 25° C @ T _A = 125° C | I _{RM} | | | | | 1 50 | | | | | | A |
| Minimum Insulation Breakdown Voltage (Circuit to Case) | V _{ISO} | | | | | 2500 | | | | | | VOLTS |
| Typical Thermal Resistance, Junction to Case | R _{θJC} | | | | | 1.10 | | | | | | °C/W |

Notes: (1) These Bridges Exhibit The Avalanche Characteristic at Breakdown. If Your Application Requires a Specific Breakdown Voltage Range, Please Contact Us.

3.01 5004P



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RATING & CHARACTERISTIC CURVES FOR SERIES DB5000P - DB5010P and SERIES ADB5004P - ADB5008P

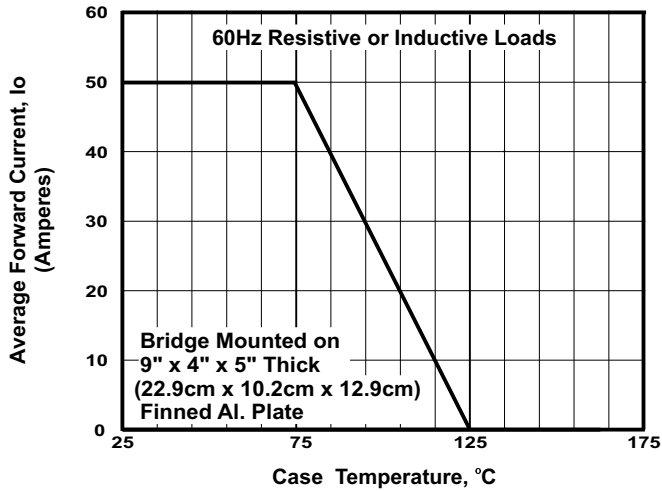


FIGURE 1. FORWARD CURRENT DERATING CURVE

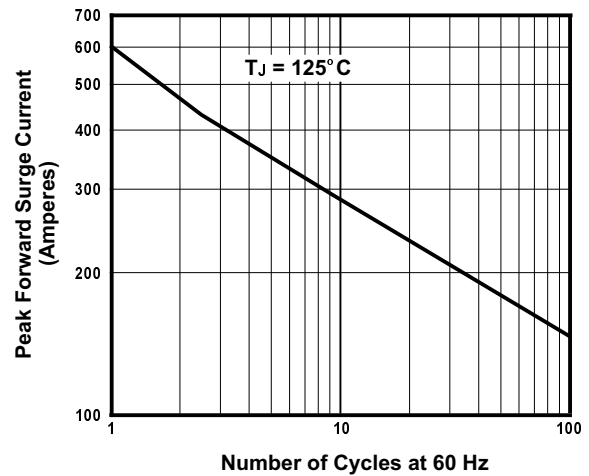


FIGURE 2. MAXIMUM NON-REPETITIVE SURGE CURRENT

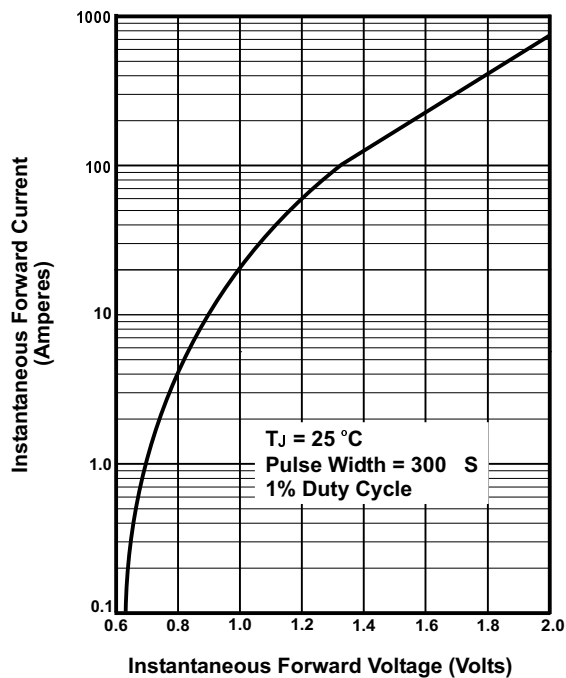


FIGURE 3. TYPICAL FORWARD CHARACTERISTIC PER DIODE

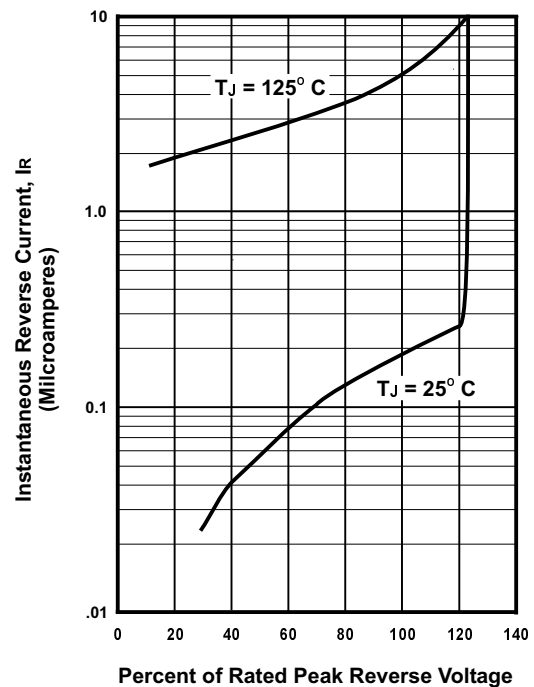


FIGURE 4. TYPICAL REVERSE CHARACTERISTICS